

Amendment
Serial No. 10/718,726
Attorney Docket No. 032125



REPLACEMENT ABSTRACT OF THE DISCLOSURE
S/N: 10/718,726

A method of manufacturing a semiconductor device including a capacitor including a pair of electrodes and a ferroelectric film with ferroelectricity sandwiched therebetween, by depositing the ferroelectric film on a first substrate; forming the capacitor by grinding the ferroelectric film and forming the electrodes so that the electrodes are perpendicular to a direction of a polarization axis of the ferroelectric film; forming a first interlayer insulating film covering a surface of the first substrate and the capacitor; forming a transistor on a second substrate, the transistor including a gate electrode and a diffusion region; forming a second interlayer insulating film covering a surface of the second substrate and the transistor; flattening surfaces of the first and second interlayer insulating films by chemical mechanical polishing; integrating the first and second substrates by joining the flattened surfaces of the first and second interlayer insulating films; and removing the first substrate.